

-20V/70mΩ@-4.5V P-Channel MOSFET

Features

- VDS(max)=-20V
- ID(max)=-3.3A
- RDS(ON) =70mΩ(max)@VGS = -4.5V
- RDS(ON) =100mΩ(max)@VGS = -2.5V
- Improved dv/dt capability
- Green Device Available
- Fast switching

Maximum Ratings (Tc = 25°C, Unless Otherwise Noted)

Parameters	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current - Continuous(TC=25°C)	I _D	-3.3	A
Drain Current - Continuous(TC=100°C)		-2.1	A
Drain Current - Pulsed	I _{DM} ¹	-13.2	A
Power Dissipation(TC=25°C)	P _D	1.56	W
Power Dissipation - Derate above 25°C		0.012	W/°C
Storage Temperature Range	T _{TSG}	-55~ 150	°C
Operating Junction Temperature Range	T _j	-55~ 150	°C

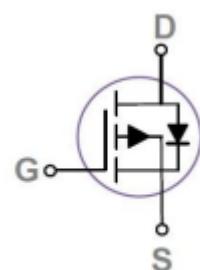
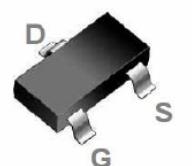
Thermal Characteristics

Parameter	Symbol	Max.	Typ.	Unit
Thermal Resistance Junction to ambient	R _{θJA}	---	80	°C/W

Applications

- Notebook
- Hand-Held Instrument
- Load Switch

SOT23 Pin Configuration



Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



HL2301DNR

Electrical Characteristics($T_j = 25^\circ\text{C}$, Unless Otherwise Noted)**Off Characteristics**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain to Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	---	---	V
BVDSS Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Reference to 25°C , $I_{\text{D}}=-1\text{mA}$	---	-0.01	---	V/ $^\circ\text{C}$
Drain-Source Leakage Current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, T_j=25^\circ\text{C}$	---	---	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 10\text{V}$	---	---	± 100	nA

On Characteristics

Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3\text{A}$	---	55	70	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-2\text{A}$	---	70	100	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.3	-0.7	-1	V

Dynamic And Switching Characteristics

Total Gate Charge ^{2,3}	Q_g	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3\text{A}$	---	4.8	---	nC
Gate-Source Charge ^{2,3}	Q_{gs}		---	0.5	---	
Gate-Drain Charge ^{2,3}	Q_{gd}		---	1.9	---	
Turn-on Delay Time ^{2,3}	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	---	3.5	---	nS
Turn-on Rise Time ^{2,3}	T_r		---	12.6	---	
Turn-off Delay Time ^{2,3}	$T_{\text{d}(\text{off})}$		---	32.6	---	
Turn-off Fall Time ^{2,3}	T_f		---	8.4	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	---	350	---	pF
Output Capacitance	C_{oss}		---	65	---	
Reverse Transfer Capacitance	C_{rss}		---	50	---	

Drain-Source Diode Characteristics And Maximum Ratings

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous Source Current	I_s	$V_G=V_D=0\text{V}, \text{Force Current}$	---	---	-3.3	A
Pulsed Source Current	I_{SM}		---	---	-13.2	A
Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1\text{A}, T_j=25^\circ\text{C}$	---	---	-1	V

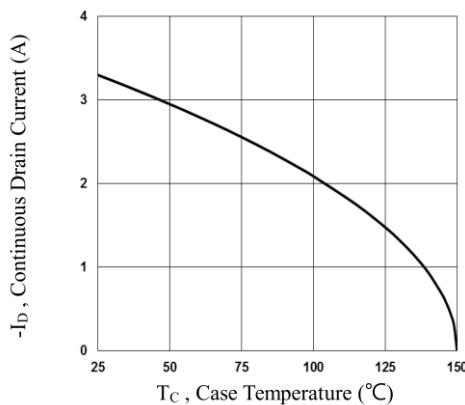


Fig.1 Continuous Drain Current vs. T_c

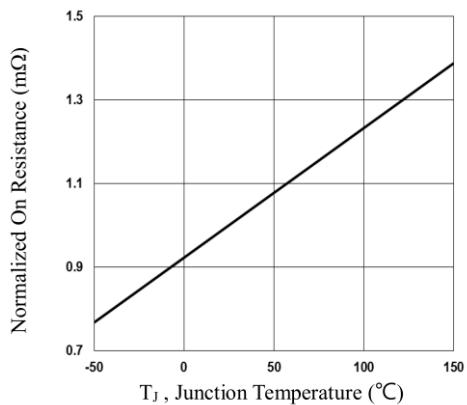


Fig.2 Normalized RD_{SON} vs. T_J

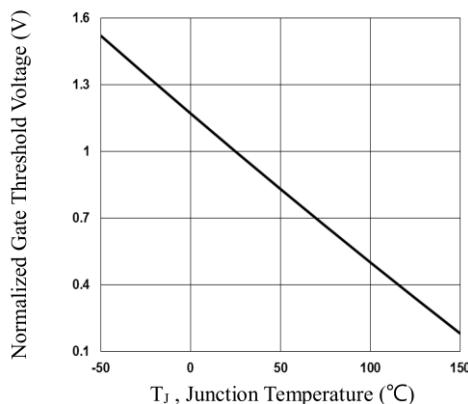


Fig.3 Normalized V_{th} vs. T_J

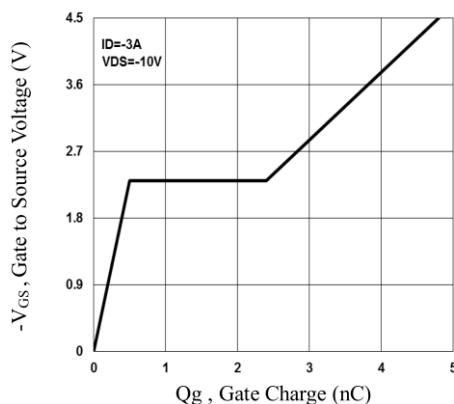


Fig.4 Gate Charge Waveform

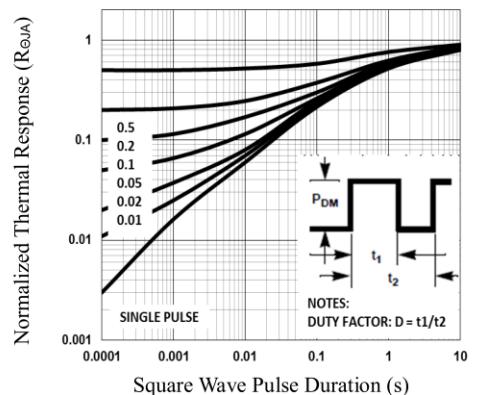


Fig.5 Normalized Transient Impedance

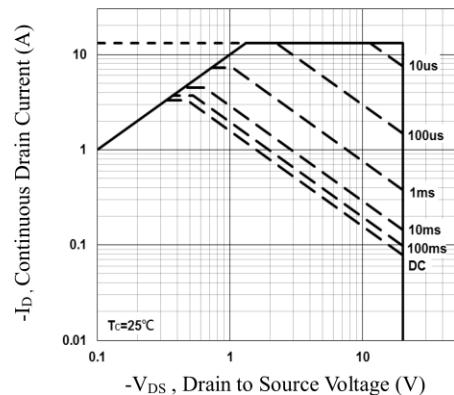


Fig.6 Maximum Safe Operation Area

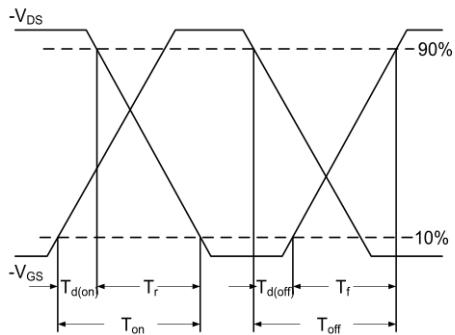


Fig.7 Switching Time Waveform

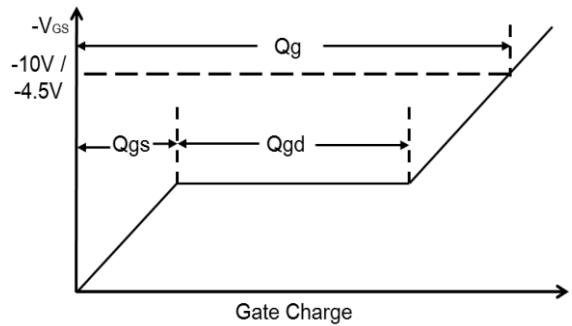
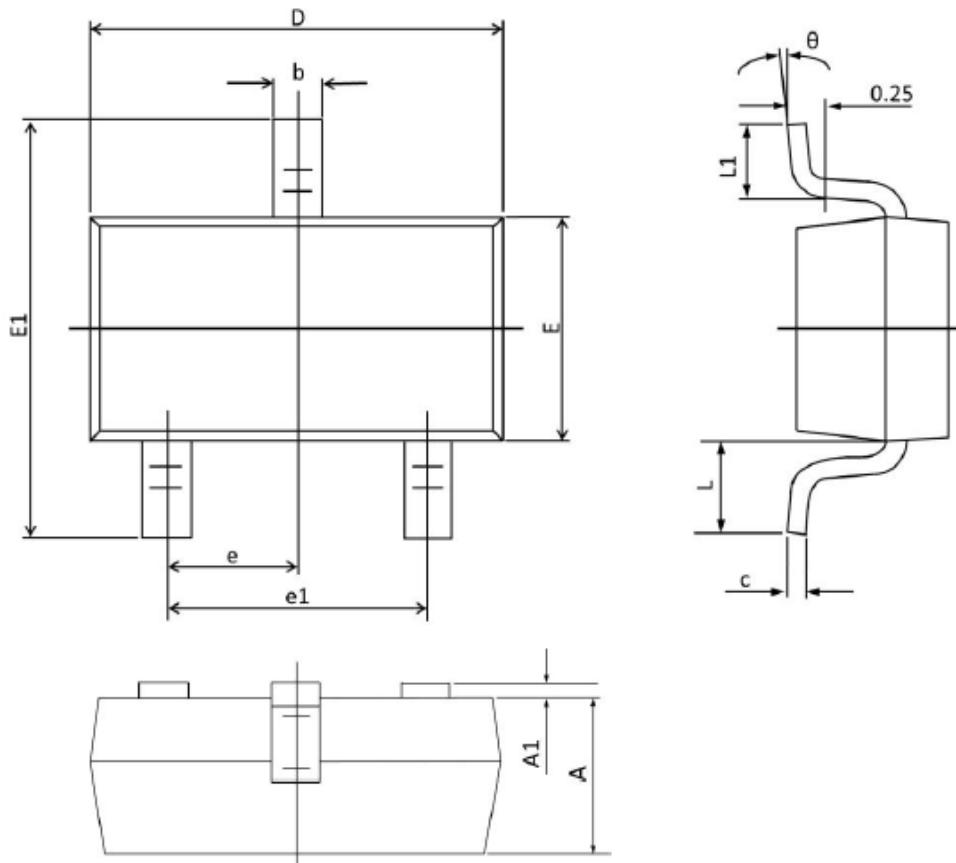


Fig.8 Gate Charge Waveform

SOT23 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°



HL2301DNR

Shen zhen Hang Lin Microelectronics Co., Ltd cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a HL product. No circuit patent license, copyrights or other intellectual property rights are implied. HL reserves the right to make changes to their products or specifications without notice. Customers are advised to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete.